



STD110NH02L

N-channel 24V - 0.0044Ω - 80A - DPAK
STripFET™ III Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D
STD110NH02L	24V	<0.0048Ω	80A ⁽¹⁾

1. Value limited by wire bonding

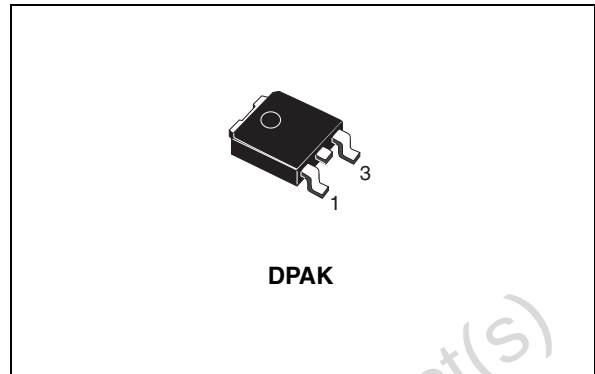
- R_{DS(on)} * Qg industry's benchmark
- Conduction losses reduced
- Switching losses reduced
- Low threshold device

Description

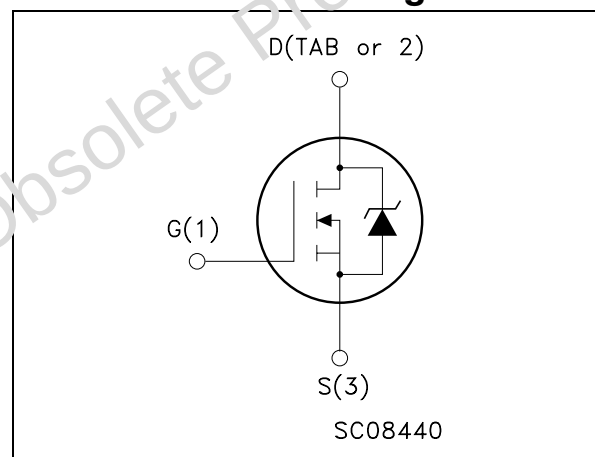
This device utilizes the latest advanced design rules of ST's proprietary STripFET™ technology. This is suitable for the most demanding DC-DC converter application where high efficiency is to be achieved.

Applications

- Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STD110NH02LT4	D110NH02L	DPAK	Tape & reel

Contents

1 **Electrical ratings** 3

2 **Electrical characteristics** 4

 2.1 Electrical characteristics (curves) 6

3 **Test circuit** 8

4 **Package mechanical data** 9

5 **Packaging mechanical data** 11

6 **Revision history** 14

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
$V_{\text{spike}}^{(1)}$	Drain-source voltage rating	30	V
V_{DS}	Drain-source voltage ($V_{\text{GS}} = 0$)	24	V
V_{DGR}	Drain-gate voltage ($R_{\text{GS}} = 20\text{K}\Omega$)	24	V
V_{GS}	Drain-source voltage	± 20	V
$I_{\text{D}}^{(2)}$	Drain current (continuous) at $T_{\text{C}} = 25^{\circ}\text{C}$	80	A
$I_{\text{D}}^{(2)}$	Drain current (continuous) at $T_{\text{C}} = 100^{\circ}\text{C}$	80	A
$I_{\text{DM}}^{(3)}$	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at $T_{\text{C}} = 25^{\circ}\text{C}$	125	W
	Derating factor	0.83	W/ $^{\circ}\text{C}$
$E_{\text{AS}}^{(4)}$	Single pulse avalanche energy	900	mJ
T_{stg}	Storage temperature	-55 to 175	$^{\circ}\text{C}$
T_{J}	Max. operating junction temperature		

1. Guaranteed when external $R_{\text{g}} = 4.7\ \Omega$ and $t_{\text{f}} < t_{\text{fmax}}$.

2. Value limited by wire bonding.

3. Pulse width limited by safe operating area

4. Starting $T_{\text{J}} = 25^{\circ}\text{C}$, $I_{\text{D}} = 30\text{A}$, $V_{\text{DD}} = 15\text{V}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case Max	1.20	$^{\circ}\text{C}/\text{W}$
R_{thJA}	Thermal resistance junction-ambient Max	100	$^{\circ}\text{C}/\text{W}$
T_{I}	Maximum lead temperature for soldering purpose	275	$^{\circ}\text{C}$

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 3. On⁽¹⁾ /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 25\text{mA}$, $V_{GS} = 0$	24			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 20$ $V_{DS} = 20$, $T_C = 125^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	1			V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{V}$, $I_D = 40\text{A}$ $V_{GS} = 5\text{V}$, $I_D = 20\text{A}$		0.0044 0.0050	0.0050 0.0095	Ω Ω

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 10\text{V}$, $I_D = 40\text{A}$		52		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 15\text{V}$, $f = 1\text{MHz}$, $V_{GS} = 0$		4450 1126 141		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 10\text{V}$, $I_D = 80\text{A}$ $V_{GS} = 10\text{V}$		69 13 9	93	nC nC nC
$Q_{oss}^{(2)}$	Output charge	$V_{DS} = 16\text{V}$, $V_{GS} = 0\text{V}$		27		nC
$Q_{gls}^{(3)}$	Third-quadrant gate charge	$V_{DS} < 0\text{V}$, $V_{GS} = 10\text{V}$		64		nC
R_G	Gate input resistance	$f = 1\text{MHz}$ gate DC Bias = 0 Test signal level = 20mV Open drain		16		Ω

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2. $Q_{oss} = C_{oss} \cdot \Delta V_{in}$, $C_{oss} = C_{gd} + C_{ds}$. See [Section Appendix A](#)

3. Gate charge for synchronous operation

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 10V$, $I_D = 40A$, $R_G = 4.7\Omega$, $V_{GS} = 10V$ <i>Figure 13 on page 8</i>		14		ns
t_r	Rise time			224		ns
$t_{d(off)}$	Turn-off delay time			69		ns
t_f	Fall time			40	54	ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				80	A
I_{SDM}	Source-drain current (pulsed)				320	A
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 40A$, $V_{GS} = 0$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 80A$, $di/dt = 100A/\mu s$, $V_{DD} = 15V$, $T_J = 150^\circ C$ <i>Figure 15 on page 8</i>		47		ns
Q_{rr}	Reverse recovery charge			58		μC
I_{RRM}	Reverse recovery current			2.5		A

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

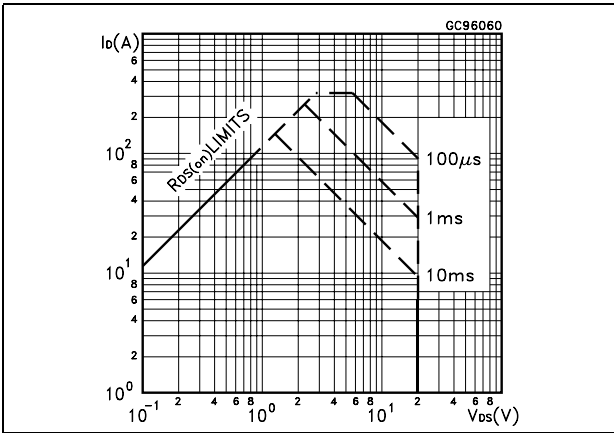


Figure 2. Thermal impedance

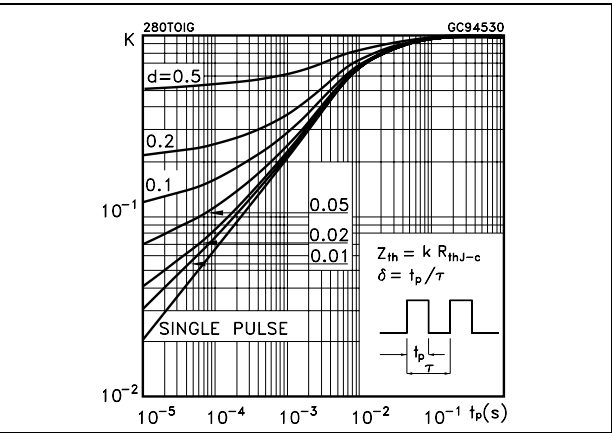


Figure 3. Output characteristics

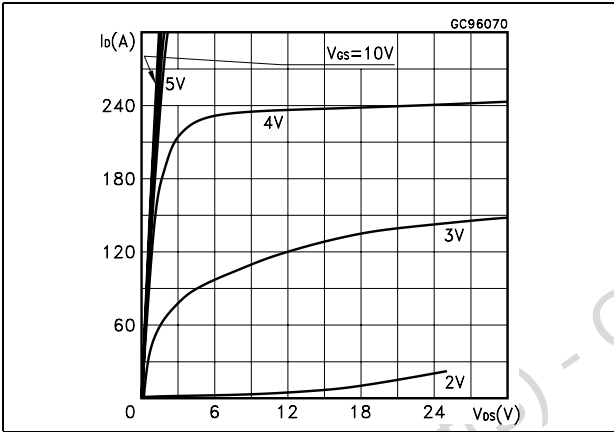


Figure 4. Transfer characteristics

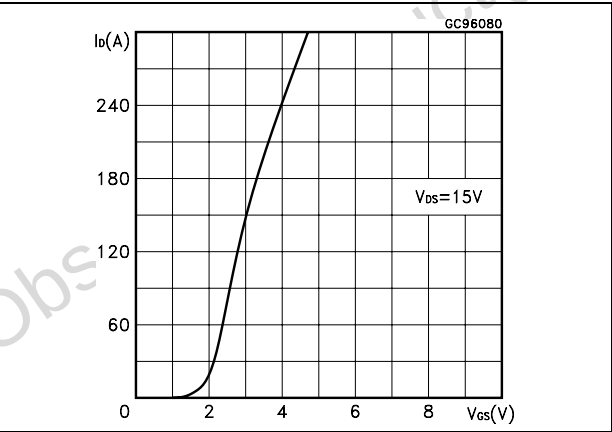


Figure 5. Transconductance

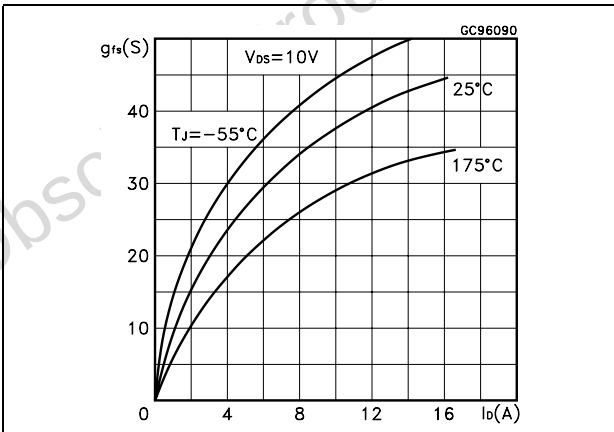


Figure 6. Static drain-source on resistance

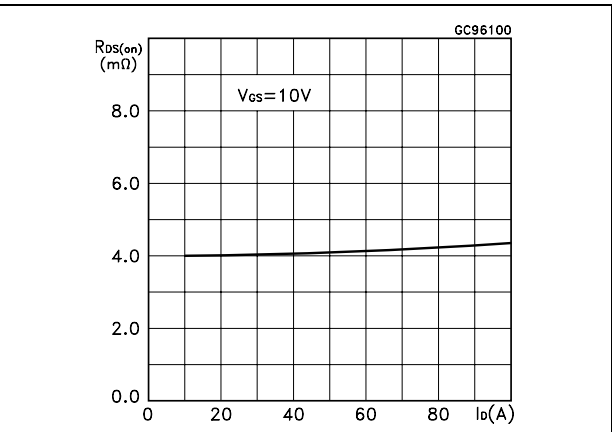


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

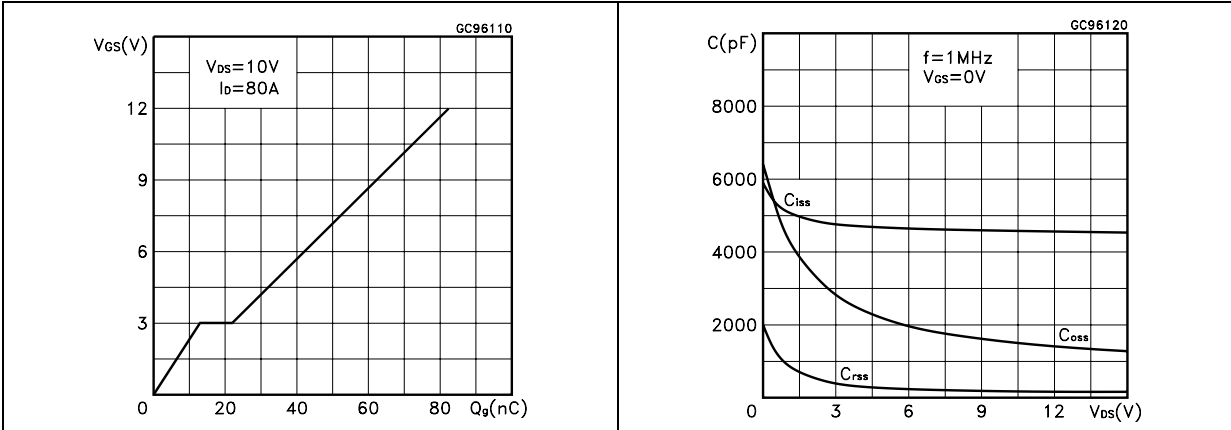


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

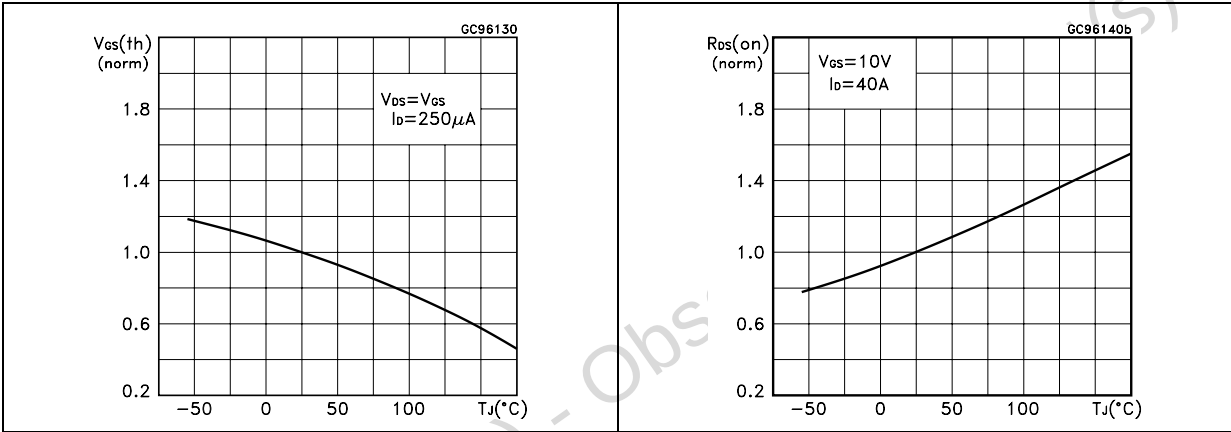
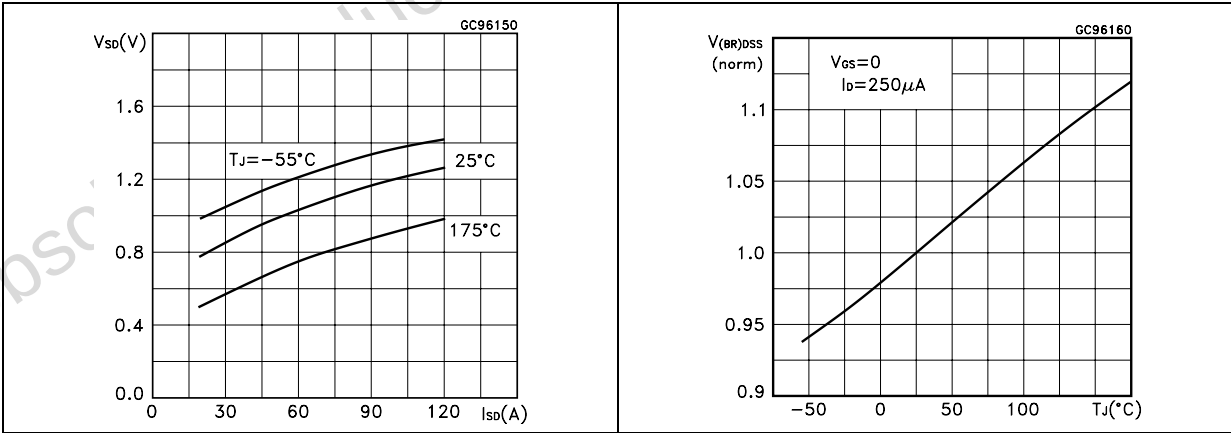


Figure 11. Source-drain diode forward characteristics Figure 12. Normalized breakdown voltage vs temperature



3 Test circuit

Figure 13. Switching times test circuit for resistive load

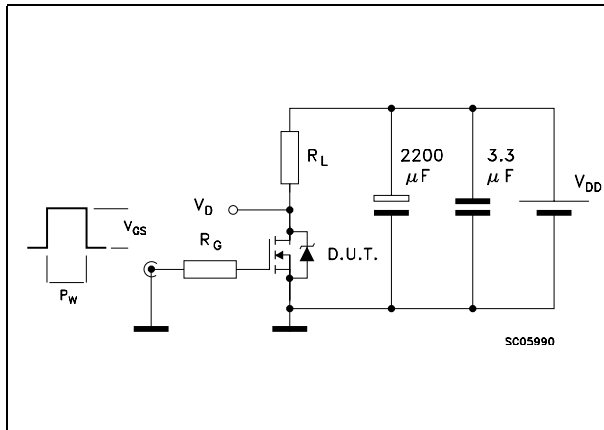


Figure 14. Gate charge test circuit

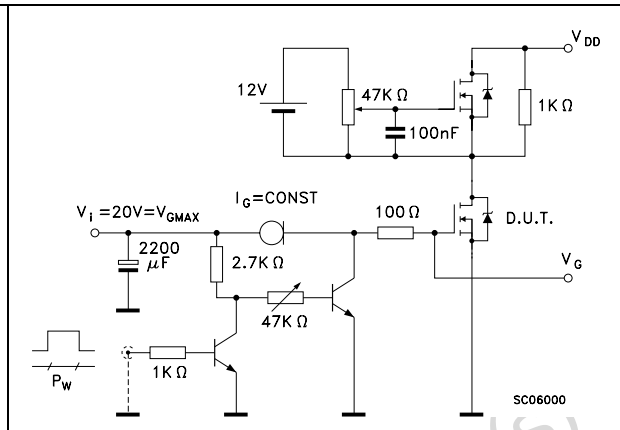


Figure 15. Test circuit for inductive load switching and diode recovery times

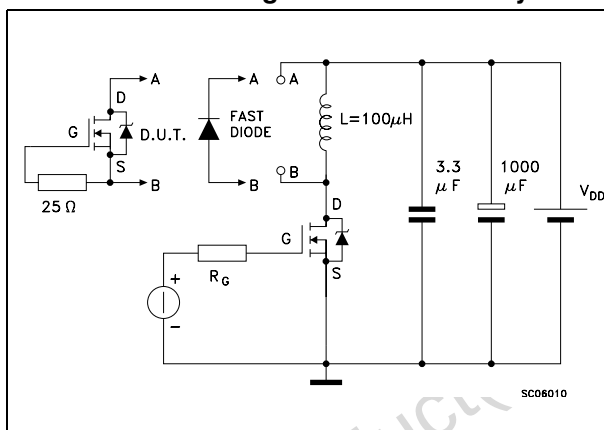


Figure 16. Unclamped Inductive load test circuit

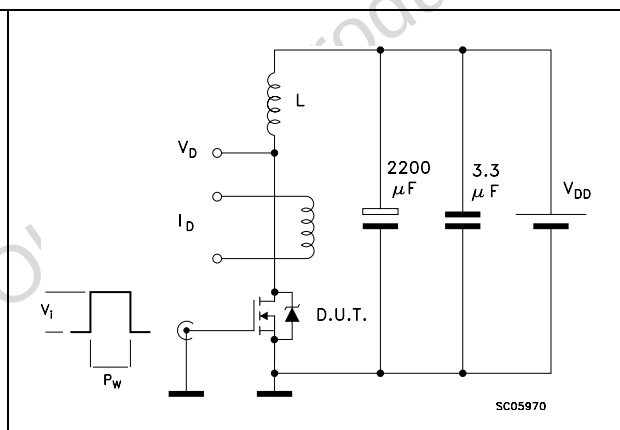
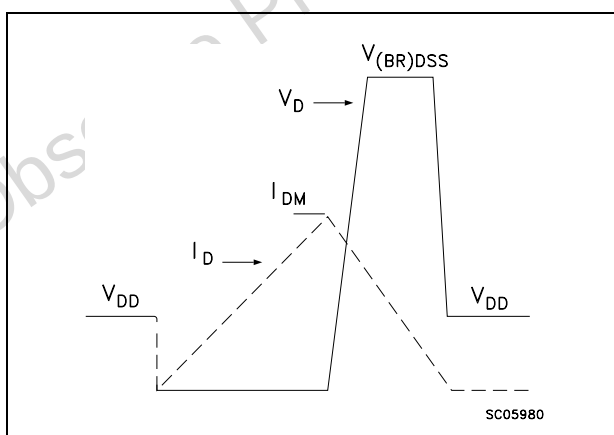


Figure 17. Unclamped inductive waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Product(s) - Obsolete Product(s)

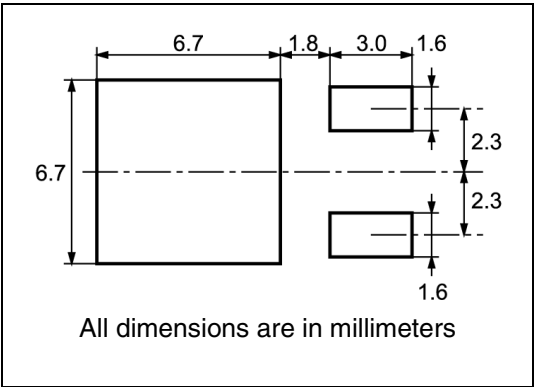
DPAK MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
e		2.28			0.090	
e1	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°

Obsole

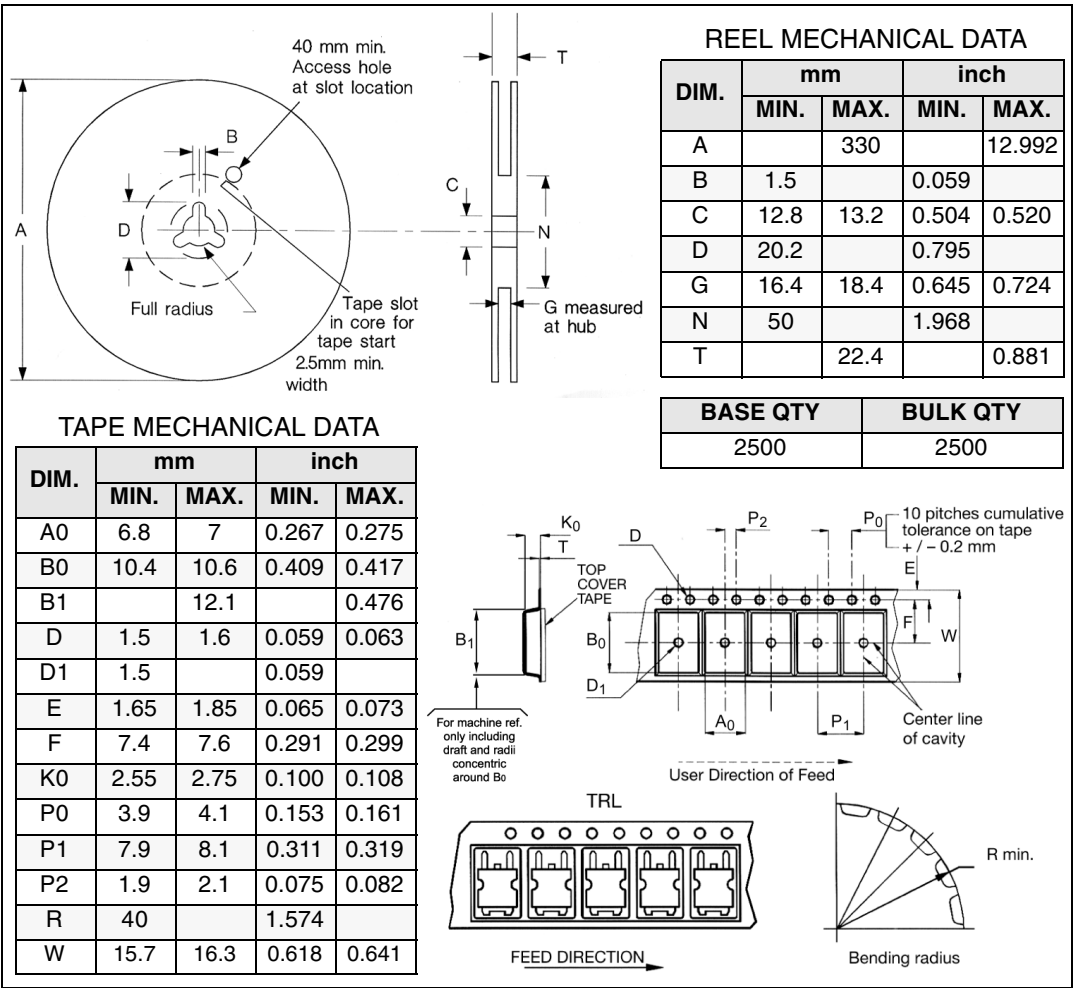
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5 Packaging mechanical data

DPAK FOOTPRINT

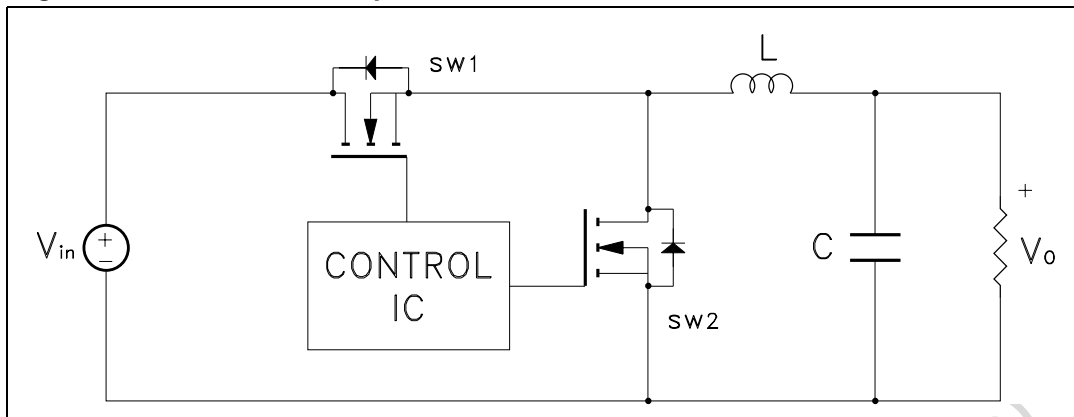


TAPE AND REEL SHIPMENT



Appendix A Buck converter - power losses estimation

Figure 18. Buck converter: power losses estimation



The power losses associated with the FETs in a synchronous buck converter can be estimated using the equations shown in the table below. The formulas give a good approximation, for the sake of performance comparison, of how different pairs of devices affect the converter efficiency. However a very important parameter, the working temperature, is not considered. The real device behavior is really dependent on how the heat generated inside the devices is removed to allow for a safer working junction temperature.

- The low side (SW2) device requires:
 - Very low $R_{DS(on)}$ to reduce conduction losses
 - Small Q_{gl} s to reduce the gate charge losses
 - Small C_{oss} to reduce losses due to output capacitance
 - Small Q_{rr} to reduce losses on SW1 during its turn-on
 - The C_{gd}/C_{gs} ratio lower than V_{th}/V_{gg} ratio especially with low drain to source voltage to avoid the cross conduction phenomenon;
- The high side (SW1) device requires:
 - Small R_g and L_s to allow higher gate current peak and to limit the voltage feedback on the gate
 - Small Q_g to have a faster commutation and to reduce gate charge losses
 - Low $R_{DS(on)}$ to reduce the conduction losses.

Table 7. Power losses calculation

		High side switching (SW1)	Low side switch (SW2)
Pconduction		$R_{DS(on)SW1} * I_L^2 * \delta$	$R_{DS(on)SW2} * I_L^2 * (1 - \delta)$
Pswitching		$V_{in} * (Q_{gsth(SW1)} + Q_{gd(SW1)}) * f * \frac{I_L}{I_g}$	Zero Voltage Switching
Pdiode	Recovery ⁽¹⁾	Not applicable	$V_{in} * Q_{rr(SW2)} * f$
	Conduction	Not applicable	$V_{f(SW2)} * I_L * t_{deadtime} * f$
Pgate(Q _G)		$Q_{g(SW1)} * V_{gg} * f$	$Q_{gls(SW2)} * V_{gg} * f$
P _{Qoss}		$\frac{V_{in} * Q_{oss(SW1)} * f}{2}$	$\frac{V_{in} * Q_{oss(SW2)} * f}{2}$

1. Dissipated by SW1 during turn-on

Table 8. Paramiters meaning

Parameter	Meaning
d	Duty-cycle
Q _{gsth}	Post threshold gate charge
Q _{gls}	Third quadrant gate charge
Pconduction	On state losses
Pswitching	On-off transition losses
Pdiode	Conduction and reverse recovery diode losses
Pgate	Gate drive losses
P _{Qoss}	Output capacitance losses

6 Revision history

Table 9. Revision history

Date	Revision	Changes
09-Sep-2004	6	Complete version
08-Aug-2006	7	New template, updated SOA

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